L11: (29) 10 and (organic.clm. or polymer.clm.)
L12: (20) 11 and (etch$3 or pattern$3)
L13: (7) 12 and ((silicon adj based) or polysiloxane or silsesquioxane)
L14: (9) (("6,324,091") or ("6,320,200") or ("6,348,700") or ("4,663,270") or
L15: (34202) 2 and electrode.clm.
L16: (0) 15 and (silicon adj based adj (mask or photoresist or resist))
L17: (14045) 15 and (resist or mask or photoresist)
L18: (658) 17 and ((mask or resist or pattern) near (organic or polymer or ser
L19: (485) 18 and ((pattern$3 or etch$3) adj2 (organic or polymer or semicond
L20: (99) 18 and ((pattern$3 or etch$3) adj2 (organic or polymer))
L21: (29) 20 and ((pattern$3 or etch$3) adj2 (organic or polymer)).clm
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20 and ((pattern$3 or etch$3) adj2 (organic or polymer)).clm.

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	S	C	P		3			In
1	✓		US 20030224611 A1	20031204	60	Manufacturing method of semiconductor devices by usi	438/706			Seta, Shoji et al.								US 2(
2			US 20030207521 A1	20031106	56	Manufacturing use of	438/200			Tanaka, Toshihiko et al.	✓							US 2(
3			US 20030165750 A1	20030904	29	Method of manufacturing electronic device	430/5	430/22; 430/311		Tanaka, Toshihiko et al.	✓							US 2(
4			US 20030151118 A1	20030814	18	Aperture masks for circuit fabrication	257/620	257/40; 257/618;		Baude, Paul F. et al.	✓							US 2(
5			US 20030052081 A1	20030320	6	METHOD FOR PRODUCING ACTIVE OR PASSIVE COMPONENTS ON A P	216/24			KOOPS, HANS WILFRIED PETER	✓							US 2(
6			US 20030048256 A1	20030313	30	Computing device with roll up components	345/168			Salmon, Peter C.	✓							US 2(
7			US 20030036293 A1	20030220	31	Method for manufacturing a semiconductor device	438/780	438/781; 438/942		Tanaka, Toshihiko et al.	✓							US 2(
8			US 20030022446 A1	20030130	18	Nonvolatile semiconductor memory device and manufactur	438/257	257/315; 257/E21.682;		Lee, Seong-Soo et al.	✓							US 2:
9			US 20030003775 A1	20030102	9	Fabrication of molecular electronic circuit by imprin	438/800			Chen, Yong	✓							US 2(
10			US 20020086232 A1	20020704	13	Electronically active primer layers for thermal patternin	430/200	430/311; 430/312;		Nirmal, Manoj et al.	✓							US 2(
11			US 20020059899 A1	20020523	60	Manufacturing method of semiconductor devices by usi	117/97	117/84; 257/E21.252;		Seta, Shoji et al.	✓							US 2(
12			US 20020052122 A1	20020502	56	Method of manufacturing a semiconductor device	438/758			Tanaka, Toshihiko et al.	✓							US 2(
13	✓		US 20010015454 A1	20010823	19	Nonvolatile semiconductor memory device and manufactur	257/315	257/314; 257/316;		Lee, Seong-soo et al.								US 2(
14	✓		US 6645856 B2	20031111	30	Method for manufacturing a semiconductor device using h	438/671	430/313; 430/5;		Tanaka, Toshihiko et al.								US
15	✓		US 6605542 B2	20030812	56	Manufacturing method of semiconductor devices by usi	438/700	257/E21.252; 257/E21.579;		Seta, Shoji et al.								US
16	✓		US 6596656 B2	20030722	54	Manufacturing use of photomasks with an opaque pa		430/5; 438/945		Tanaka, Toshihiko et al.								US
17	✓		US 6583000 B2	20030624	18	Nonvolatile semiconductor memory device and manufactur	438/257	257/E21.682; 257/E27.103;		Lee, Seong-soo et al.								US

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L3: (12603) 2 and organic
L4: (1038) 3 and (organic near polymer)
L5: (400) 4 and (organic.clm.)
L6: (93) 5 and (((organic or polymer) adj2 semiconductor) or (semiconductor a·
L7: (60) 6 and (resist or photoresist or pattern)
L8: (60) 6 and (resist or photoresist or mask)
L9: (28) 8 and (organic adj2 (memory or device))
L10: (43) 3 and ((organic adj memory) or (polymer adj memory))
L11: (29) 10 and (organic.clm. or polymer.clm.)
L12: (20) 11 and (etch$3 or pattern$3)
L13: (7) 12 and ((silicon adj based) or polysiloxane or silsesquioxane)
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12 and ((silicon adj based) or polysiloxane or silsesquioxane)

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	S	C	P		3		Ima
1	☐	☑	US 20040002176 A1	20040101	17	Organic ferroelectric memory	438/40	257/40		Xu, Baomin	☑	☐	☐	☐	☐	☐	US 2004
2	☐	☐	US 20030113766 A1	20030619	94	Amine activated colorimetric resonant biosensor	435/6			Pepper, Jane W. et al.	☑	☐	☐	☐	☐	☐	US 200:
3	☐	☐	US 20030092075 A1	20030515	90	Aldehyde chemical surface activation processes and tes	435/7.9	427/2.11		Pepper, Jane	☑	☐	☐	☐	☐	☐	US 200:
4	☐	☐	US 20030027328 A1	20030206	91	Guided mode resonant filter biosensor using a linear gra	435/287.2	435/6; 435/7.9		Cunningham, Brian T. et al.	☑	☐	☐	☐	☐	☐	US 200:
5	☐	☐	US 20030027327 A1	20030206	83	Optical detection of label-free biomolecular inte	435/287.2	356/319; 435/6;		Cunningham, Brian T. et al.	☑	☐	☐	☐	☐	☐	US 200:
6	☐	☐	US 20020127565 A1	20020912	89	Label-free high-throughput optical technique for detect	435/6	435/287.2; 435/7.9		Cunningham, Brian et al.	☑	☐	☐	☐	☐	☐	US 2002
7	☐	☐	US 6528815 B1	20030304	10	Write-once read-many electrical memory element of	257/40	257/390; 257/529;		Brown, Adam R. et al.	☑	☐	☐	☐	☐	☐	US (

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